

WS7918DC

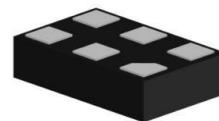
CMOS High Gain GPS LNA

<http://www.sh-willsemi.com>

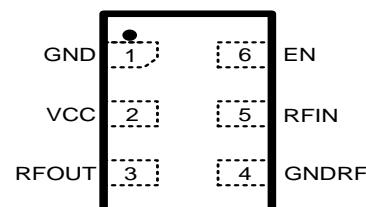
Descriptions

The WS7918DC is a low noise amplifier (LNA) for GPS receiver applications, available in a small 6-pin DFN package. The WS7918DC requires only one external inductor for input matching.

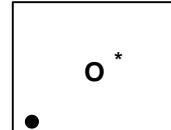
The WS7918DC is designed to achieve low power dissipation and good performance.



DFN1109-6L (Bottom view)



Pin configuration (Top view)



O = Device code

* = Month code (A~Z)

Marking (Top view)

Applications

- Cell phones
- Tablets
- Other RF front-end modules

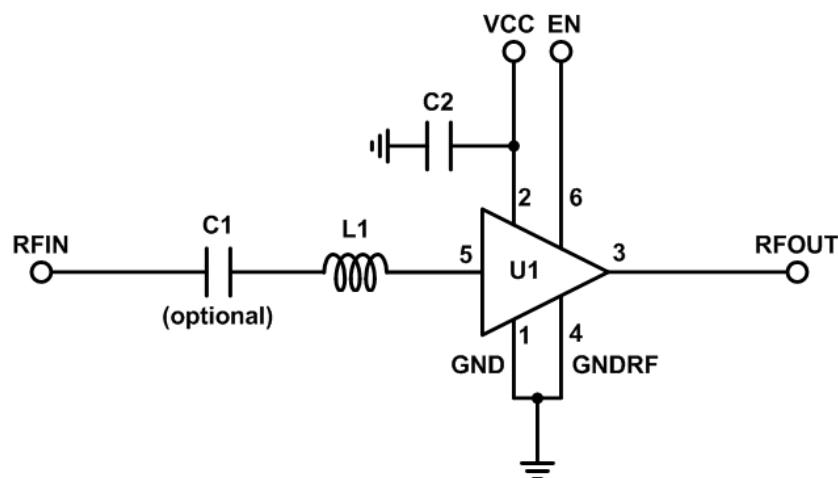
Order information

Device	Package	Shipping
WS7918DC-6/TR	DFN1109-6L	3000/Reel&Tape

Pinning Information

Pin	Description	Transparent top view	Symbol view
1	GND		
2	VCC		
3	RFOUT		
4	GNDRF		
5	RFIN		
6	EN		

Application Information



Symbol	Description	Footprint	Value	Supplier	Comment
U1	WS7918DC	1.1x0.9x0.45 mm ³	NA	Will-Semi	DUT
C1	Capacitor	0402	1 nF	Various	DC blocking
C2	Capacitor	0402	1 nF	Various	Supply decoupling
L1	Inductor	0402	10 nH	Murata LQW15	Input matching

Quick Reference Data

freq = 1575.42 MHz; V_{CC} = 2.8 V; V_{EN} > 1.2 V; Temp = 25°C; input matched to 50 Ω with a 10 nH inductor. The condition is applied unless otherwise specified.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{CC}	Supply voltage		1.6	2.8	3.1	V
I _{CC}	Supply current			7.5		mA
G _p	Power gain			16.5		dB
NF	Noise figure			0.65		dB
IP _{1dB}	Input power at 1dB gain compression			-5.0		dBm
IIP ₃	Input third-order intercept point			+5.0		dBm

Recommended Operating Conditions

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{CC}	Supply voltage		1.6	2.8	3.1	V
Temp	Ambient temperature		-40	+25	+85	°C
V _{EN}	Input voltage on pin 6 (EN)	OFF state	0		0.3	V
		ON state	1.2		V _{CC}	V

Absolute Maximum Ratings

Maximum ratings are absolute ratings, exceeding only one of these values may cause irreversible damage to the integrated circuit.

Symbol	Parameter	Condition	Min	Max	Unit
V _{CC}	Supply voltage		-0.3	3.3	V
V _{EN}	Input voltage on pin EN		-0.3	3.3	V
V _{RFIN}	Input voltage on pin RFIN		-0.3	3.3	V
V _{RFOUT}	Input voltage on pin RFOUT		-0.3	3.3	V
P _{in}	RF input power			0	dBm
T _{STG}	Storage temperature		-65	+150	°C
T _J	Junction temperature			150	°C
V _{ESD}	ESD capability all pins	Human Body Model (HBM)		±2000	V

Characteristics

$1550 \text{ MHz} \leq f \leq 1615 \text{ MHz}$; $V_{CC} = 2.8 \text{ V}$; $V_{EN} > 1.2 \text{ V}$; Temp = 25°C ; input mated to 50Ω with a 10 nH inductor; The condition is applied unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	Supply current	On state		7.5		mA
		Off state		8.0	10.0	μA
G_p	Power gain	$f = 1575 \text{ MHz}$		16.5		dB
RL_{in}	Input return loss	$f = 1575 \text{ MHz}$		6.5		dB
RL_{out}	Output return loss	$f = 1575 \text{ MHz}$		18.0		dB
ISL	Reverse isolation	$f = 1575 \text{ MHz}$		27.0		dB
NF	Noise figure	$f = 1575 \text{ MHz}$		0.65		dB
$IP_{1\text{dB}}$	Input power at 1 dB gain compression	$f = 1575 \text{ MHz}$		-5.0		dBm
IIP_3	Input third-order intercept point ^[1]			+5.0		dBm
K	Rollett stability factor ^[2]		1			
t_{on}	Turn-on time				5	μs
t_{off}	Turn-off time				5	μs

[1] $f_1 = 1713 \text{ MHz}$, $f_2 = 1851 \text{ MHz}$, $P_{in} = -20 \text{ dBm}$

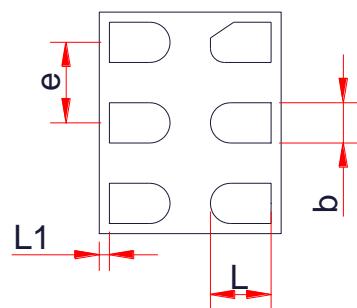
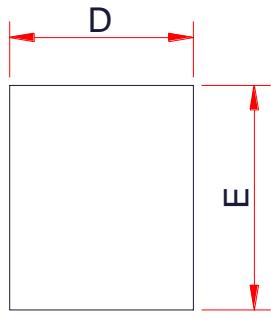
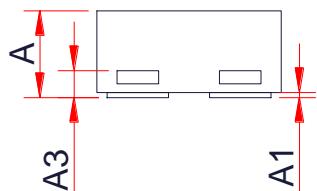
[2] 10M~20GHz

$1550 \text{ MHz} \leq f \leq 1615 \text{ MHz}$; $V_{CC} = 1.8 \text{ V}$; $V_{EN} > 1.2 \text{ V}$; Temp = 25°C ; input mated to 50Ω with a 10 nH inductor; The condition is applied unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	Supply current	On state		8.0		mA
		Off state		4.5	5.5	μA
G_p	Power gain	$f = 1575 \text{ MHz}$		16.0		dB
RL_{in}	Input return loss	$f = 1575 \text{ MHz}$		6.3		dB
RL_{out}	Output return loss	$f = 1575 \text{ MHz}$		18.0		dB
ISL	Reverse isolation	$f = 1575 \text{ MHz}$		26.0		dB
NF	Noise figure	$f = 1575 \text{ MHz}$		0.65		dB
IP_{1dB}	Input power at 1 dB gain compression	$f = 1575 \text{ MHz}$		-7.0		dBm
IIP_3	Input third-order intercept point ^[1]			+3.0		dBm
K	Rollett stability factor ^[2]		1			
t_{on}	Turn-on time				5	μs
t_{off}	Turn-off time				5	μs

[1] $f_1 = 1713 \text{ MHz}$, $f_2 = 1851 \text{ MHz}$, $P_{in} = -20 \text{ dBm}$

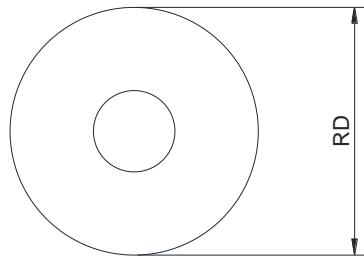
[2] 10M~20GHz

Package Outline Dimensions
DFN1109-6L

TOP VIEW
BOTTOM VIEW

SIDE VIEW

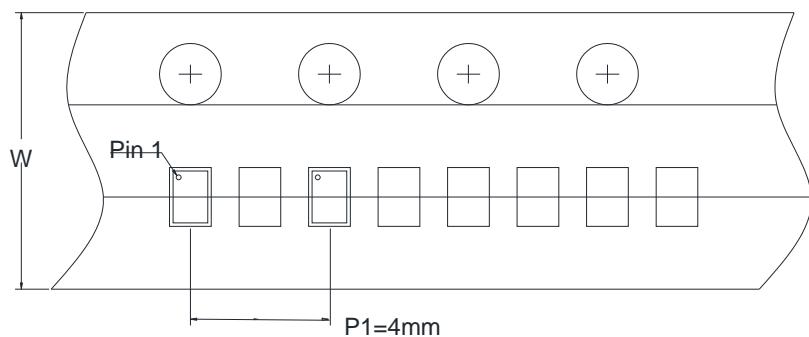
Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.40	0.45	0.50
A1	0.00	0.02	0.05
A3	0.15 Ref.		
b	0.15	0.20	0.25
D	0.80	0.90	1.00
E	1.00	1.10	1.20
e	0.40 BSC		
L	0.22	-	0.35
L1	0.05 Ref.		

Tape & Reel Dimensions

Reel Dimensions

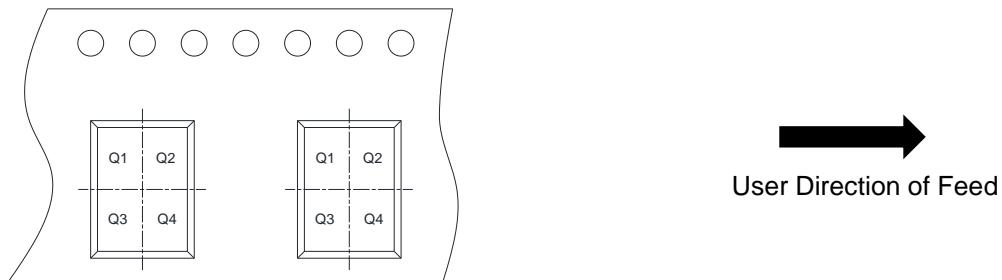


Tape Dimensions



Note: Tape material is plastic. Pitch between successive cavity centers is 2mm.

Quadrant Assignments For PIN1 Orientation In Tape



RD	Reel Dimension	<input checked="" type="checkbox"/> 7inch <input type="checkbox"/> 13inch
W	Overall width of the carrier tape	<input checked="" type="checkbox"/> 8mm <input type="checkbox"/> 12mm <input type="checkbox"/> 16mm
P1	Pitch between successive chip centers	<input type="checkbox"/> 2mm <input checked="" type="checkbox"/> 4mm <input type="checkbox"/> 8mm
Pin1	Pin1 Quadrant	<input checked="" type="checkbox"/> Q1 <input type="checkbox"/> Q2 <input type="checkbox"/> Q3 <input type="checkbox"/> Q4